



# PJS6604

## 30V Complementary Enhancement Mode MOSFET

**Voltage**

30 / -30V

**Current**

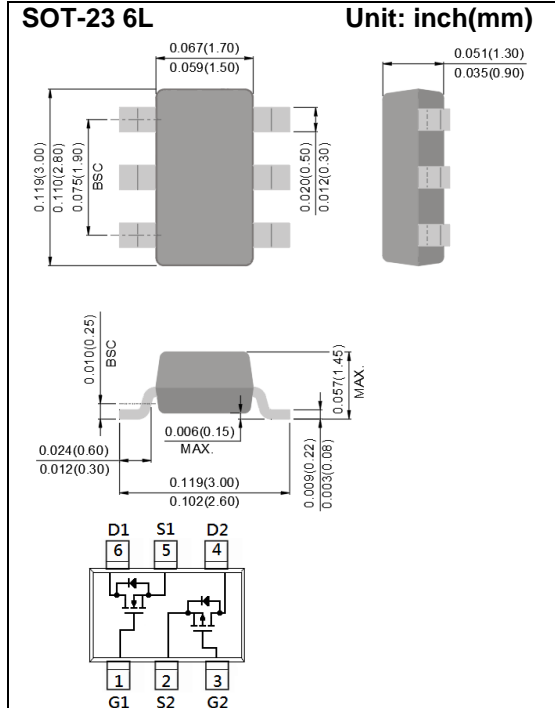
4.4 / -3.1A

### Features

- Advanced Trench Process Technology
- Specially Designed for Switch Load, PWM Application, etc.
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

### Mechanical Data

- Case: SOT-23 6L Package
- Terminals: Solderable per MIL-STD-750, Method 2026
- Approx. Weight: 0.0005 ounces, 0.014 grams



### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	N-Ch LIMIT	P-Ch LIMIT	UNITS
Drain-Source Voltage	V <sub>DS</sub>	30	-30	V
Gate-Source Voltage	V <sub>GS</sub>	±12	±12	V
Continuous Drain Current	I <sub>D</sub>	4.4	-3.1	A
Pulsed Drain Current <sup>(Note 4)</sup>	I <sub>DM</sub>	17.6	-12.4	A
Power Dissipation	P <sub>D</sub>	T <sub>a</sub> =25°C		1.25
		Derate above 25°C		10
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55~150		°C
Typical Thermal Resistance	R <sub>θJA</sub>			100
- Junction to Ambient <sup>(Note 3)</sup>				



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## N-Channel Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
<b>Static</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	30	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	0.4	0.72	1.2	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =4.4A	-	37	48	mΩ
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =3.6A	-	40	53	
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =2.5A	-	48	66	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =30V, V <sub>GS</sub> =0V	-	-	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V	-	-	±100	nA
<b>Dynamic</b> <sup>(Note 5)</sup>						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =15V, I <sub>D</sub> =4.4A, V <sub>GS</sub> =10V <sup>(Note 1,2)</sup>	-	11.3	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	1	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	1.2	-	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =15V, V <sub>GS</sub> =0V, f=1.0MHZ	-	447	-	pF
Output Capacitance	C <sub>oss</sub>		-	34	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	22	-	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =15V, I <sub>D</sub> =4.4A, V <sub>GS</sub> =10V, R <sub>G</sub> =3Ω <sup>(Note 1,2)</sup>	-	1.7	-	ns
Turn-On Rise Time	t <sub>r</sub>		-	38	-	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	82	-	
Turn-Off Fall Time	t <sub>f</sub>		-	64	-	
<b>Drain-Source Diode</b>						
Maximum Continuous Drain-Source Diode Forward Current	I <sub>S</sub>	---	-	-	1.5	A
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =1.0A, V <sub>GS</sub> =0V	-	0.77	1.2	V

**NOTES :**

1. Pulse width ≤ 300us, Duty cycle ≤ 2%
2. Essentially independent of operating temperature typical characteristics.
3. R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
4. The maximum current rating is package limited.
5. Guaranteed by design, not subject to production testing



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## P-Channel Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
<b>Static</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =-250uA	-30	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =-250uA	-0.5	-0.96	-1.3	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =-10V, I <sub>D</sub> =-3.1A	-	82	98	mΩ
		V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-2.2A	-	91	114	
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-1.1A	-	115	165	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V	-	-	-1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±12V, V <sub>DS</sub> =0V	-	-	±100	nA
<b>Dynamic</b> (Note 5)						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =-15V, I <sub>D</sub> =-3.1A, V <sub>GS</sub> =-10V (Note 1,2)	-	11	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	0.85	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	1.4	-	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =0V, f=1.0MHZ	-	443	-	pF
Output Capacitance	C <sub>oss</sub>		-	38	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	25	-	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =-15V, I <sub>D</sub> =-3.1A, V <sub>GS</sub> =-10V, R <sub>G</sub> =6Ω (Note 1,2)	-	2.5	-	ns
Turn-On Rise Time	t <sub>r</sub>		-	32	-	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	161	-	
Turn-Off Fall Time	t <sub>f</sub>		-	73	-	
<b>Drain-Source Diode</b>						
Maximum Continuous Drain-Source Diode Forward Current	I <sub>S</sub>	---	-	-	-1.5	A
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =-1.0A, V <sub>GS</sub> =0V	-	-0.79	-1.2	V

**NOTES :**

1. Pulse width ≤ 300us, Duty cycle ≤ 2%
2. Essentially independent of operating temperature typical characteristics.
3. R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins mounted on a 1 inch FR-4 with 2oz. square pad of copper.
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## N-Channel TYPICAL CHARACTERISTIC CURVES

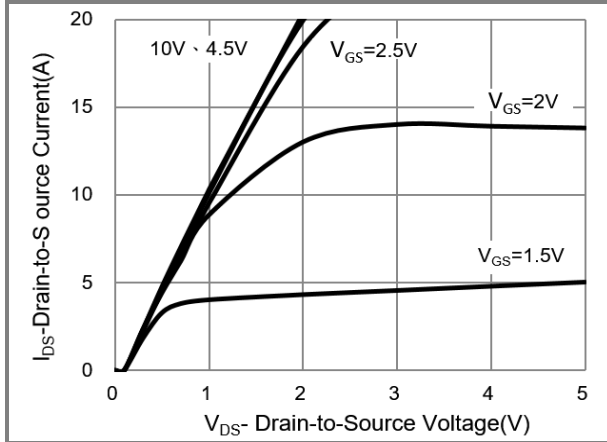


Fig.1 On-Region Characteristics

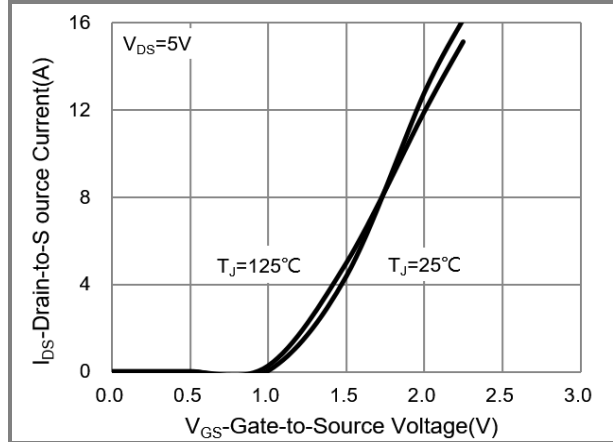


Fig.2 Transfer Characteristics

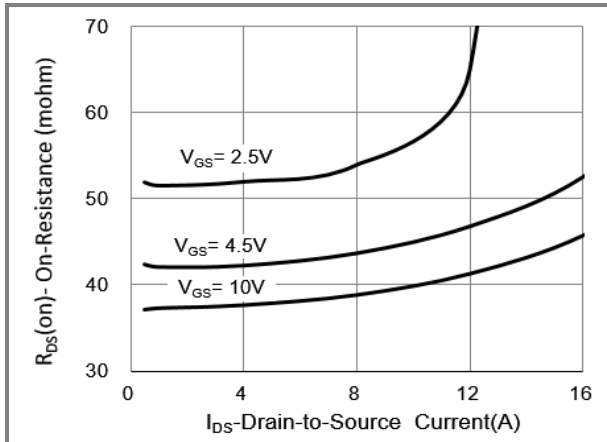


Fig.3 On-Resistance vs. Drain Current

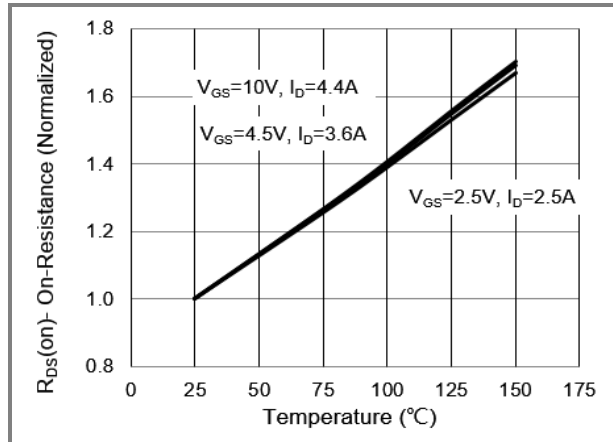


Fig.4 On-Resistance vs. Junction temperature

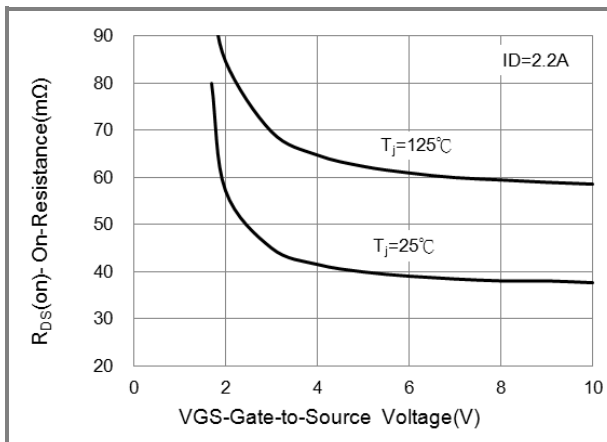


Fig.5 On-Resistance Variation with VGS.

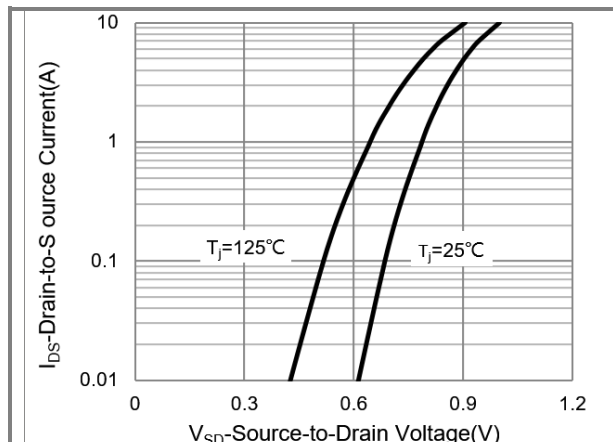


Fig.6 Body Diode Characteristics



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## N-Channel TYPICAL CHARACTERISTIC CURVES

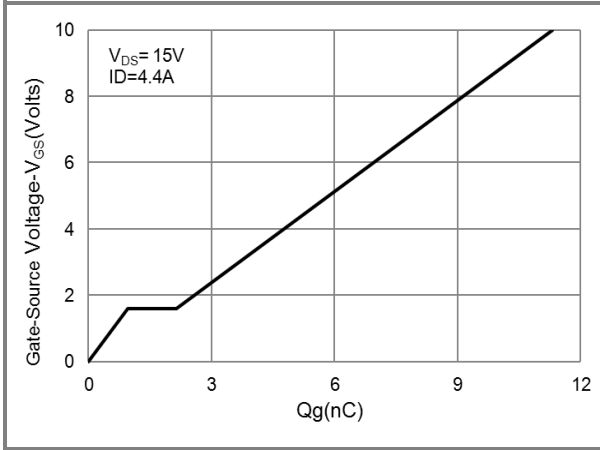


Fig.7 Gate-Charge Characteristics

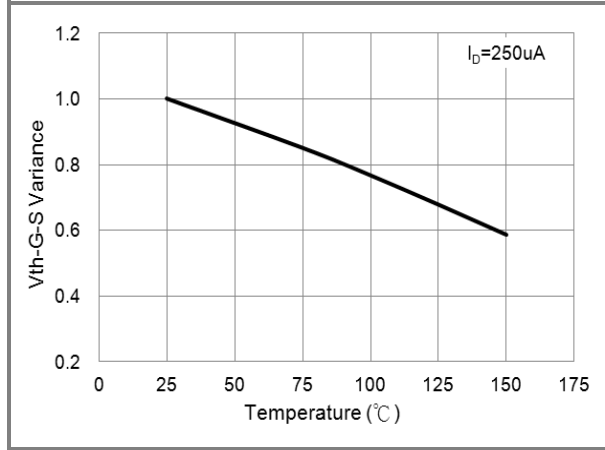


Fig.8 Threshold Voltage Variation with Temperature.

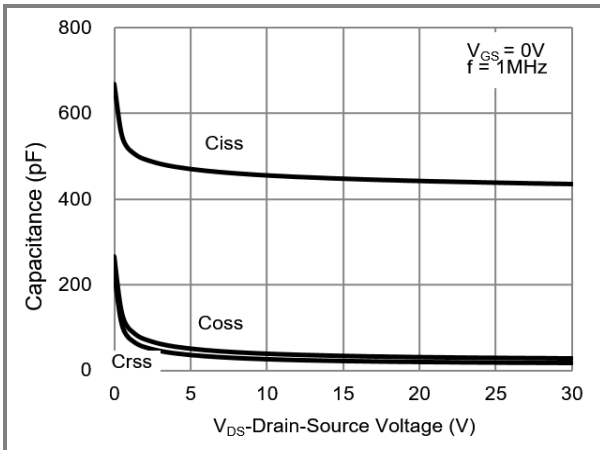


Fig.9 Capacitance vs. Drain-Source Voltage.



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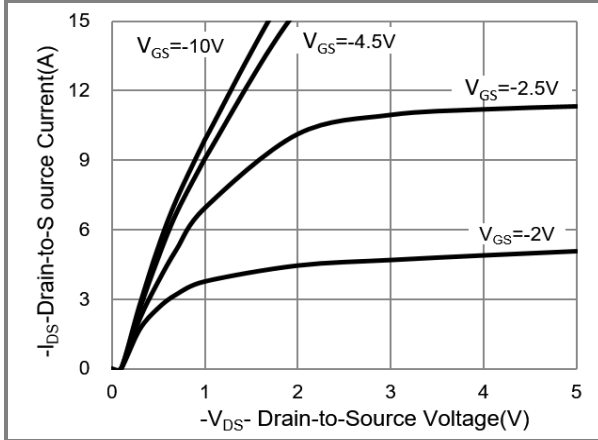


Fig.1 On-Region Characteristics

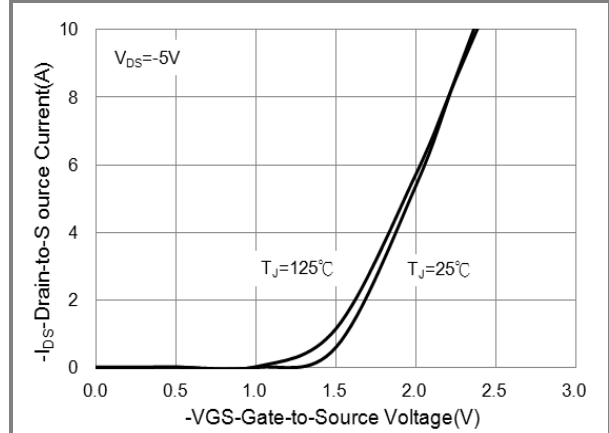


Fig.2 Transfer Characteristics

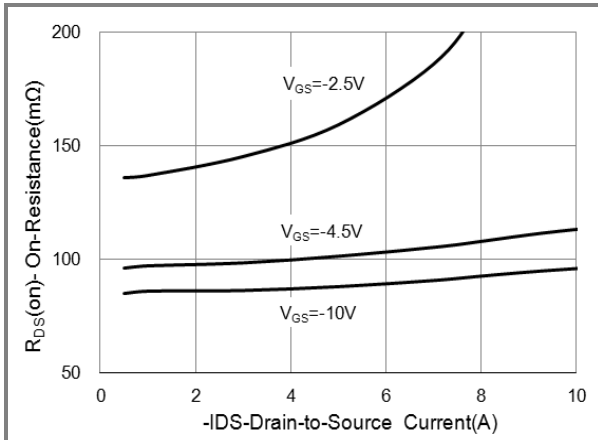


Fig.3 On-Resistance vs. Drain Current

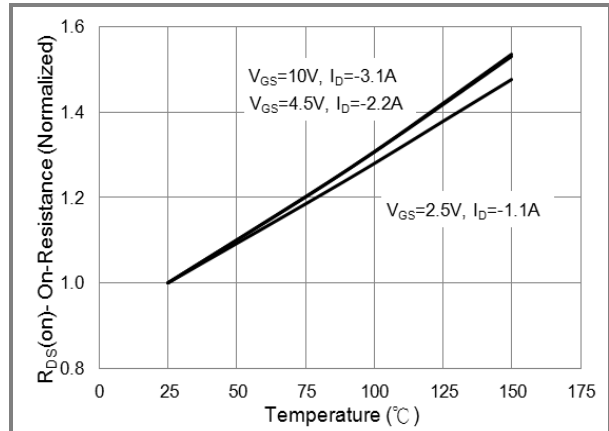


Fig.4 On-Resistance vs. Junction temperature

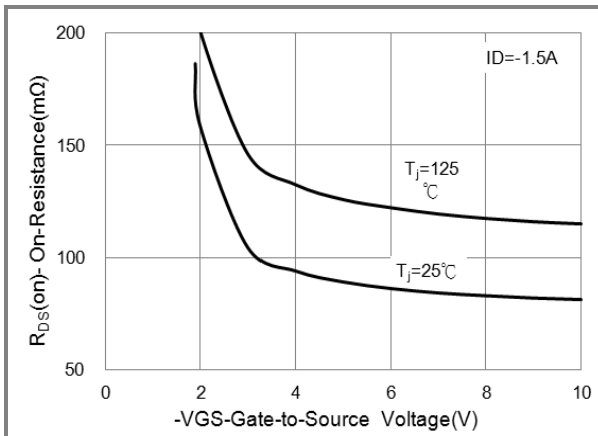


Fig.5 On-Resistance Variation with VGS.

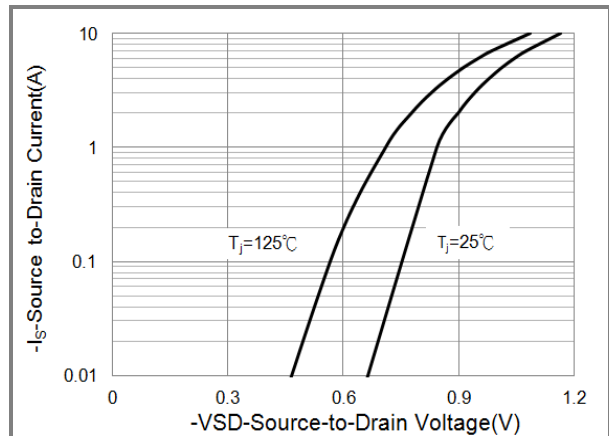


Fig.6 Body Diode Characteristics



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## P-Channel TYPICAL CHARACTERISTIC CURVES

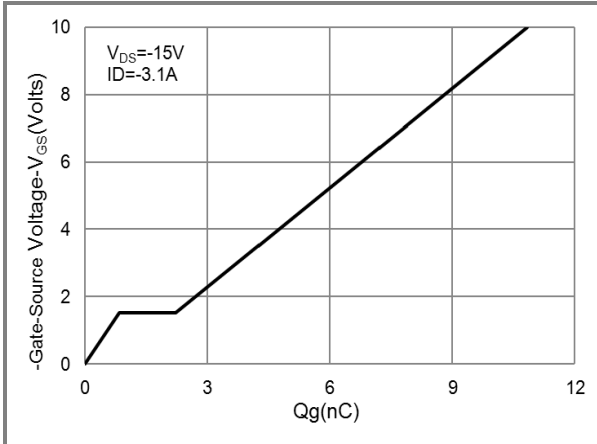


Fig.7 Gate-Charge Characteristics

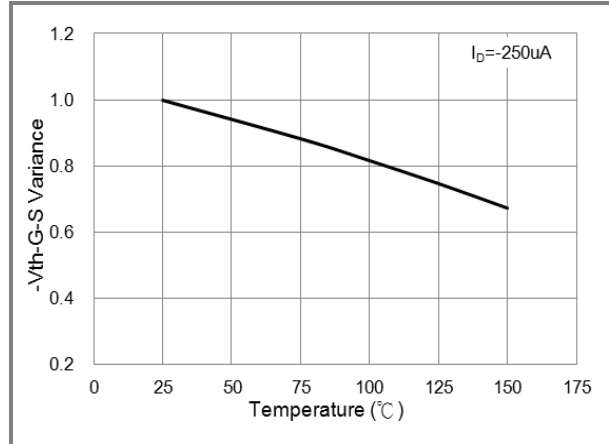


Fig.8 Threshold Voltage Variation with Temperature.

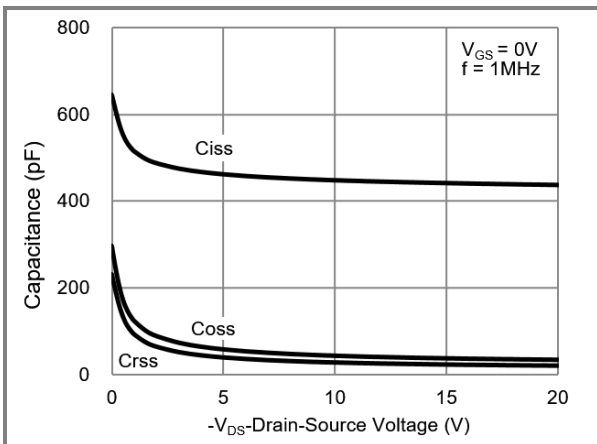


Fig.9 Threshold Voltage Variation with Temperature.

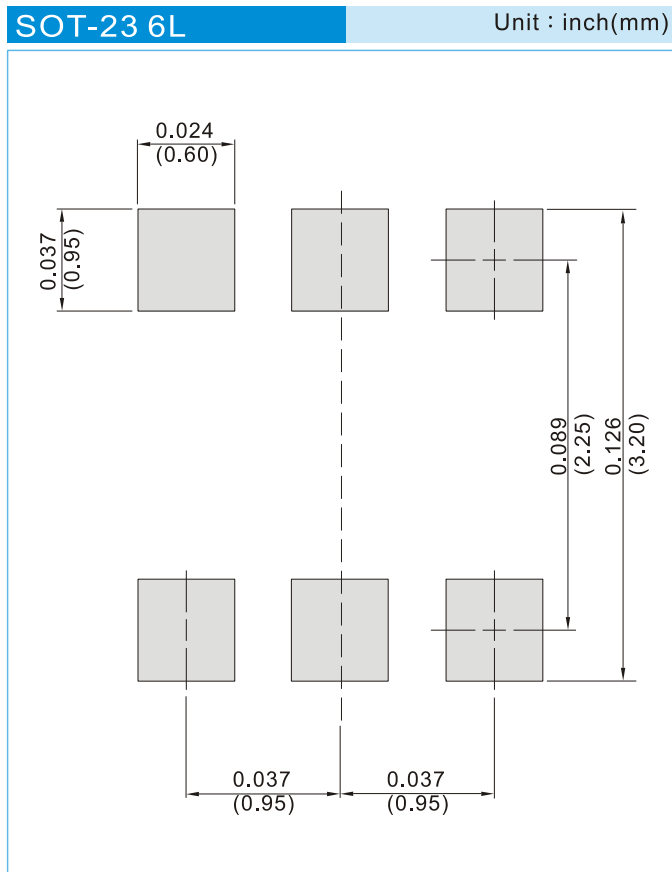


# PJS6604

## PART NO. PACKING CODE VERSION

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJS6604_S1_00001	SOT-23 6L	3K pcs / 7" reel	SC4	Halogen free RoHS compliant
PJS6604_S2_00001	SOT-23 6L	10K pcs / 13" reel	SC4	Halogen free RoHS compliant

## MOUNTING PAD LAYOUT







## PJS6604

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